

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-15 (canceled)

Claim 16 (new): An active matrix circuit comprising:

a semiconductor layer;
a p-type impurity region provided in said semiconductor layer; and
an interlayer insulating film comprising silicon nitride provided over said semiconductor layer.

Claim 17 (new): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 18 (new): A circuit according to claim 16 wherein said active matrix circuit is incorporated into an image sensor.

Claim 19 (new): A circuit according to claim 16 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

Claim 20 (new): A circuit according to claim 16 wherein said semiconductor layer comprises a crystal silicon.

Claim 21 (new): An active matrix circuit comprising:

a semiconductor layer;
a p-type impurity region provided in said semiconductor layer; and
an interlayer insulating film comprising a silicon nitride layer and a silicon oxide layer,
said interlayer insulating film provided over said semiconductor layer.

Claim 22 (new): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 23 (new): A circuit according to claim 21 wherein said active matrix circuit is incorporated into an image sensor.

Claim 24 (new): A circuit according to claim 21 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device

Claim 25 (new): A circuit according to claim 21 wherein said semiconductor layer comprises a crystal silicon.

Claim 26 (new): An active matrix circuit comprising:
a semiconductor layer;
a p-type impurity region provided in said semiconductor layer; and
a conductive layer comprising titanium and aluminum over said interlayer insulating film.

Claim 27 (new): A circuit according to claim 26 wherein said conductive layer comprises an electrode.

Claim 28 (new): A circuit according to claim 26 wherein said conductive layer comprises a wiring.

Claim 29 (new): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal display.

Claim 30 (new): A circuit according to claim 26 wherein said active matrix circuit is incorporated into an image sensor.

Claim 31 (new): A circuit according to claim 26 wherein said active matrix circuit is incorporated into a liquid-crystal electro-optical device.

Claim 32 (new): A circuit according to claim 26 wherein said semiconductor layer comprises a crystal silicon.

Claim 33 (new): A circuit according to claim 26 wherein said titanium and said aluminum are formed in a multi-layer film.